Data Sheet

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Manufacturers of World Class Discrete Semiconductors

2N6724
2N6725

NPN SILICON DARLINGTON
POWER TRANSISTOR

JEDEC TO-237 CASE (EBC)

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N6724, 2N6725 are Silicon NPN Darlington Power Transistors designed for amplifier applications.

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

	SYMBOL	2N6724	2N6725	UNIT
Collector-Base Voltage	V_{CBO}	50	60	V
Collector-Emitter Voltage	V_{CEO}	40	50	V
Emitter-Base Voltage	V_{EBO}	12		V
Collector Current	I_C	2.0		A
Base Current	I_B	500		mA
Power Dissipation(T_C=25°C)	P_D	2.0		W
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 TO +150		°C
Thermal Resistance	θJC	62.5		°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C)

		2N6724		2N6725		
SYMBOL	TEST CONDITIONS	MIN	MAX	MIN	MAX	UNIT
I_{CBO}	V_{CB}=30V		0.1		-	μA
I_{CBO}	V_{CB}=40V		-		0.1	μA
I_{EBO}	V_{EB}=10V		0.1		0.1	μA
BV_{CBO}	I_C=1.0μA	50		60		V
BV_{EBO}	I_E=10μA	12		12		V
BV_{CES}	I_C=1.0mA	40		50		V
$V_{CE(SAT)}$	I_C=1.0A, I_B=2.0mA		1.5		1.5	V
$V_{BE(ON)}$	V_{CE}=5.0V, I_C=1.0A		2.0		2.0	V
h_{FE}	V_{CE}=5.0V, I_C=200mA	25,000		25,000		
h_{FE}	V_{CE}=5.0V, I_C=1.0A	4,000	40,000	4,000	40,000	
f_T	V_{CE}=5.0V, I_C=200mA, f=100MHz	1.0	10	1.0	10	MHz
C_{ob}	V_{CB}=10V, I_E=0, f=1.0MHz		10		10	pF

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